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(54) **PEALD NITRIDE FILMS**

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(71) Applicant: **Applied Materials, Inc.**, Santa Clara, CA (US)

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(72) Inventors: **Hanhong Chen**, Milpitas, CA (US);
Philip A. Kraus, San Jose, CA (US);
Joseph AuBuchon, San Jose, CA (US)

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(73) Assignee: **Applied Materials, Inc.**, Santa Clara, CA (US)

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(57) **ABSTRACT**

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A method of depositing nitride films is disclosed. Some embodiments of the disclosure provide a PEALD process for depositing nitride films which utilizes separate reaction and nitridation plasmas. In some embodiments, the nitride films have improved growth per cycle (GPC) relative to films deposited by thermal processes or plasma processes with only a single plasma exposure. In some embodiments, the nitride films have improved film quality relative to films deposited by thermal processes or plasma processes with only a single plasma exposure.

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